

MMBTA13LT1, MMBTA14LT1

MMBTA14LT1 is a Preferred Device

Darlington Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	30	Vdc
Collector–Base Voltage	V_{CBO}	30	Vdc
Emitter–Base Voltage	V_{EBO}	10	Vdc
Collector Current – Continuous	I_C	300	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	$^\circ\text{C}$

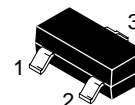
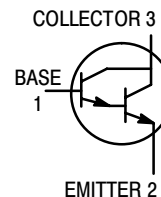
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- FR–5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



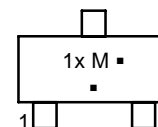
ON Semiconductor®

<http://onsemi.com>



SOT–23 (TO–236)
CASE 318
STYLE 6

MARKING DIAGRAM



- 1x = Device Code
 x = M for MMBTA13LT1
 x = N for MMBTA14LT1
 M = Date Code*
 ■ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA13LT1	SOT–23	3,000 / Tape & Reel
MMBTA13LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel
MMBTA14LT1	SOT–23	3,000 / Tape & Reel
MMBTA14LT1G	SOT–23 (Pb–Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBTA13LT1, MMBTA14LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu\text{A}$ dc, $V_{BE} = 0$)	$V_{(BR)CES}$	30	–	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	100	nAdc
ON CHARACTERISTICS (Note 3)				
DC Current Gain ($I_C = 10 \text{ mA}$ dc, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mA}$ dc, $V_{CE} = 5.0 \text{ Vdc}$)	MMBTA13 MMBTA14 MMBTA13 MMBTA14	h_{FE}	5000 10,000 10,000 20,000	– – – –
Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mA}$ dc, $I_B = 0.1 \text{ mA}$ dc)	$V_{CE(sat)}$	–	1.5	Vdc
Base – Emitter On Voltage ($I_C = 100 \text{ mA}$ dc, $V_{CE} = 5.0 \text{ Vdc}$)	V_{BE}	–	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (Note 4) ($I_C = 10 \text{ mA}$ dc, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	125	–	MHz

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$.

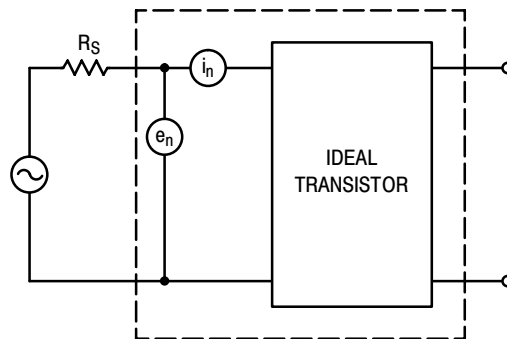


Figure 1. Transistor Noise Model

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NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

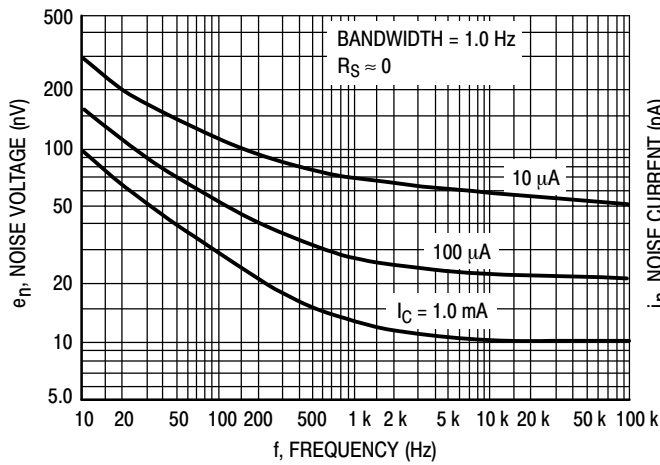


Figure 2. Noise Voltage

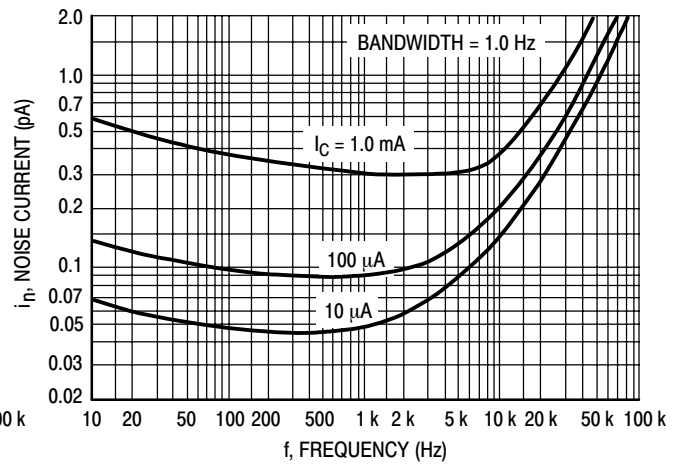


Figure 3. Noise Current

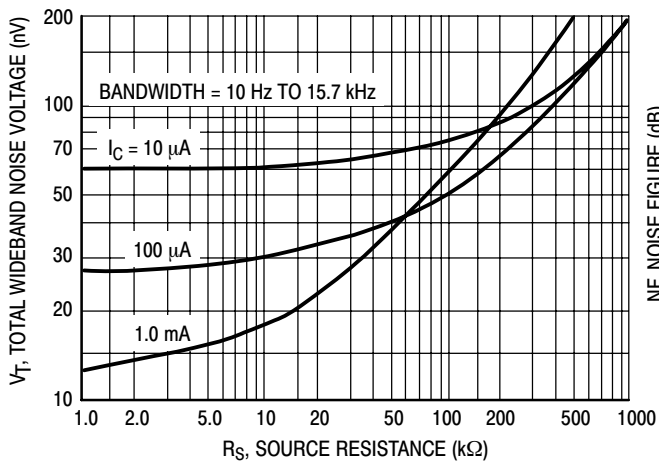


Figure 4. Total Wideband Noise Voltage

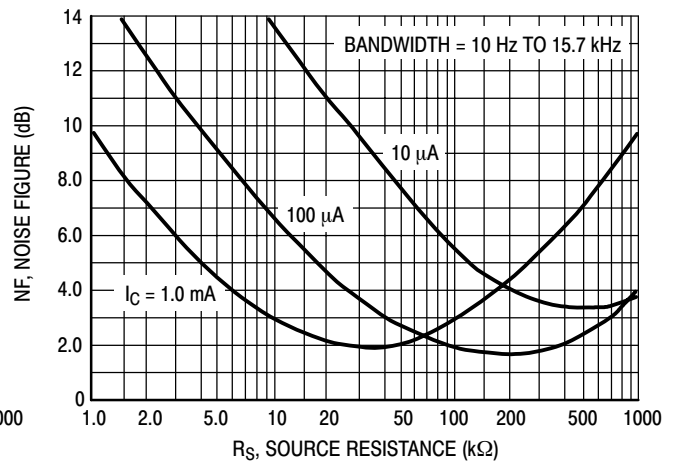


Figure 5. Wideband Noise Figure

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SMALL-SIGNAL CHARACTERISTICS

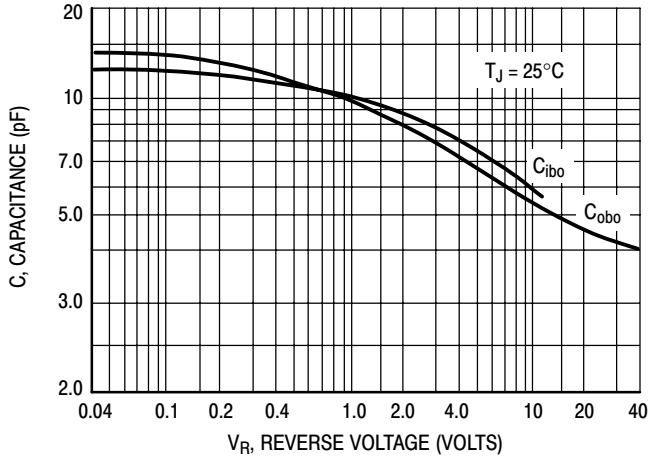


Figure 6. Capacitance

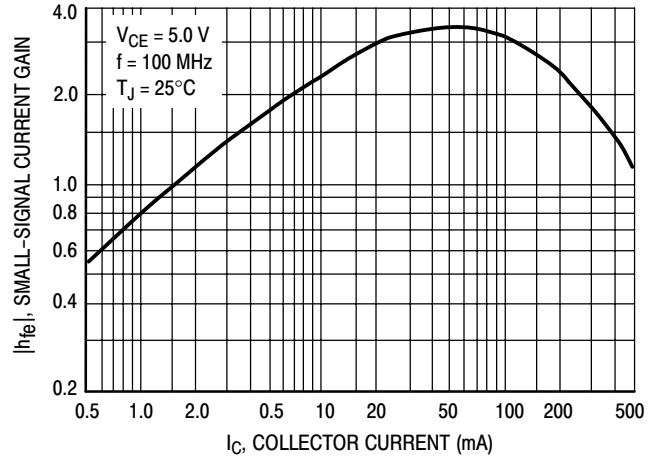


Figure 7. High Frequency Current Gain

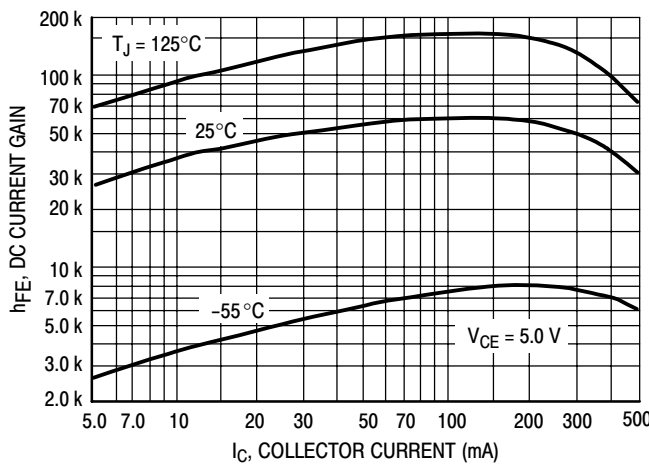


Figure 8. DC Current Gain

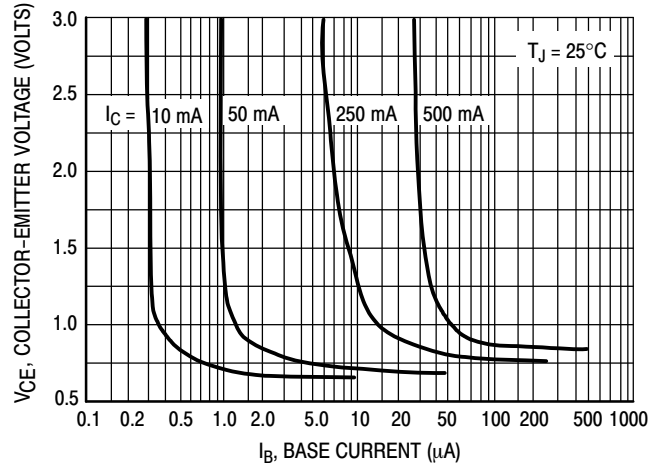


Figure 9. Collector Saturation Region

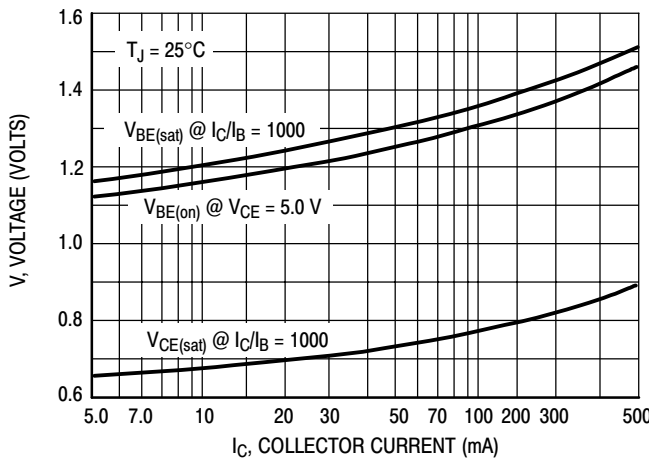


Figure 10. "On" Voltages

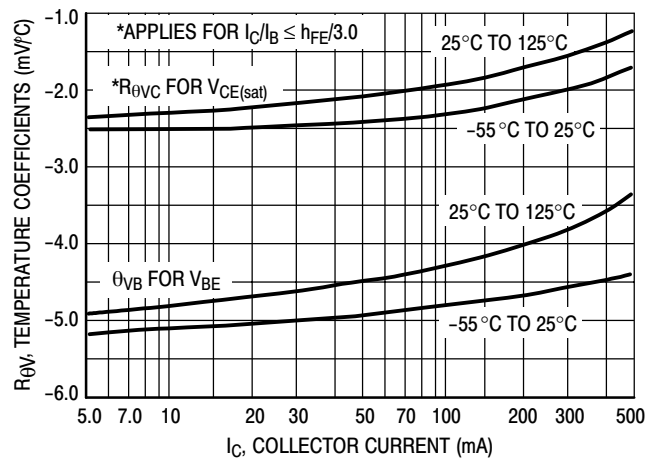


Figure 11. Temperature Coefficients

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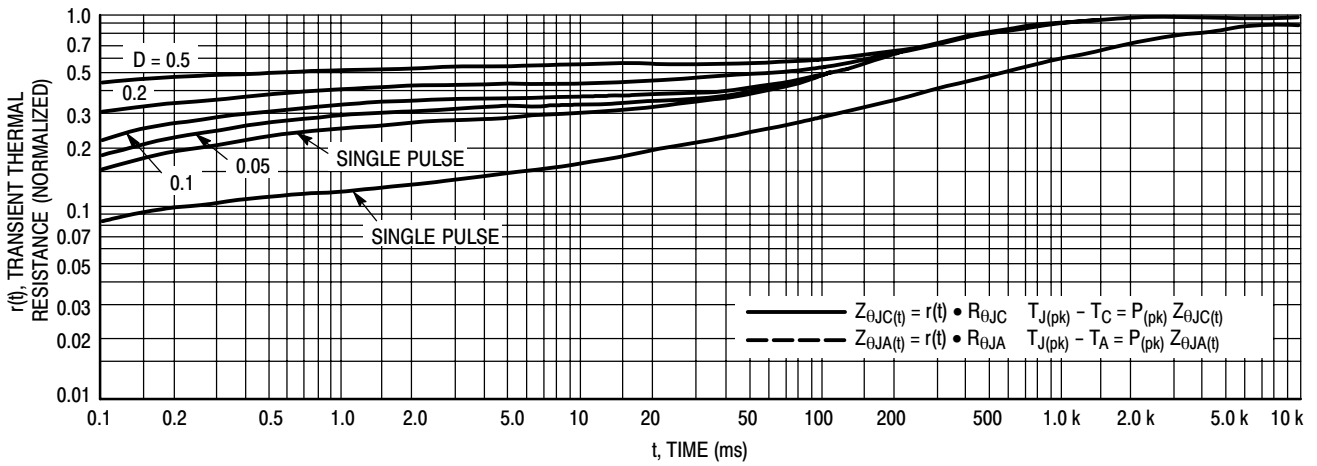


Figure 12. Thermal Response

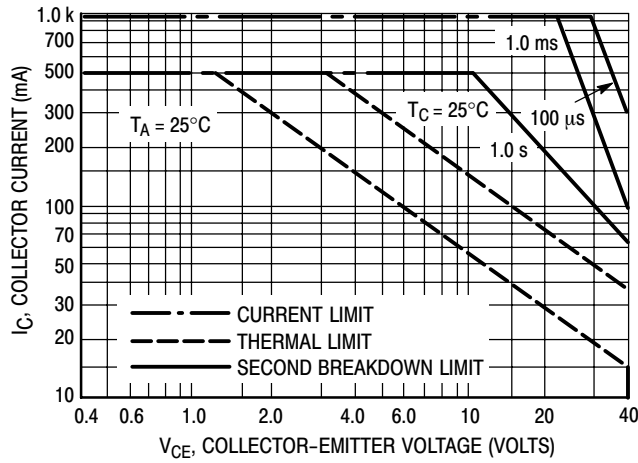
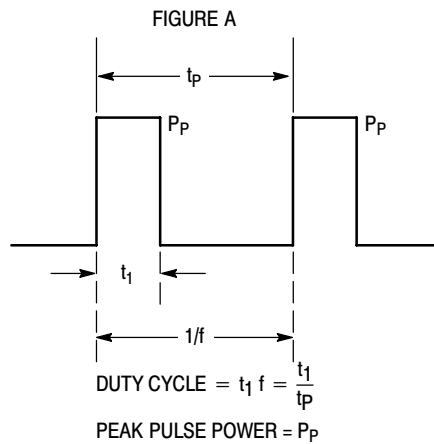


Figure 13. Active Region Safe Operating Area

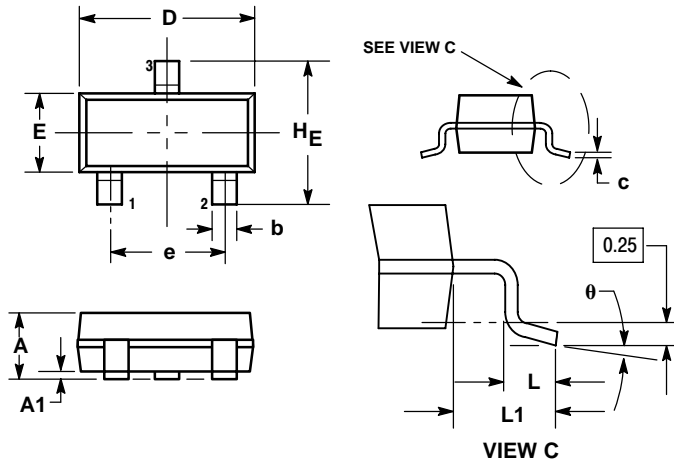


Design Note: Use of Transient Thermal Resistance Data

MMBTA13LT1, MMBTA14LT1

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AN



NOTES:

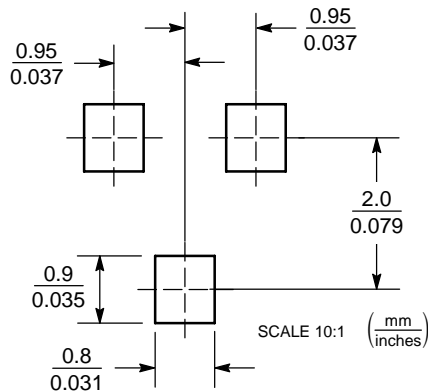
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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